

## Product Overview

### MBRD5H100T4G: Schottky Power Rectifier, Switch-mode, 5.0 A, 100 V

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large metal to silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes and polarity protection diodes.

### Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured - Not Sheared!
- NBRD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### Applications

- Power Supplies

### End Products

- Power Supplies

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	$V_{RRM}$ Min (V)	$V_F$ Max (V)	$I_{RM}$ Max ( $\mu$ A)	$I_{O(rec)Max}$ (A)	$I_{FSM}$ Max (A)	$t_{rr}$ Max (ns)	$C_j$ Max (pF)	Package Type
MBRD5H100T4G	0.3735	Pb-free Halide free	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3
NBRD5H100T4G		AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3
NBRD5H100T4G-VF01		AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	100	0.71	3.5	5	105	-	-	DPAK-3

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